

10/808833

	Hits	Search Text	DBs	Time Stamp
1	73302	tft or (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:29
2	3151	first adj2 S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:29
3	2311	second adj2 S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:30
4	31990	average near4 grain near4 (diameter or size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:31
5	98231	active near3 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:32
6	1581	S2 same S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:35
7	2	S4 same S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 11:39
8	1854	S2 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:35
9	12	S4 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/07 17:35
10	73302	tft or (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 11:40
11	3151	first adj2 S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 11:40

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12	2311	second adj2 S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 11:40
13	31990	average near4 grain near4 (diameter or size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 11:40
14	1581	S12 same S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 16:05
15	98231	active near3 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 11:41
16	8038	S15 near4 thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 13:42
17	110057	(different or differing or differed) near3 characteristic s	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 13:45
18	6	S17 same S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 13:45
19	138	S18 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:06
20	360086	grain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:06
21	71	S20 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:06
22	1071	257/57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:15

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23	1890	257/66	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:16
24	655	257/69	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:16
25	234	257/70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:19
26	3778	257/347	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:19
27	508	257/352	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:19
28	2799	257/59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:19
29	7538	S23 or S24 or S25 or S26 or S27 or S28 or S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/08 17:19
30	48	S20 and S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:14
31	5898	first adj3 gate adj3 (insulating or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:15
32	68438	gate adj3 (insulating or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:15
33	146	S32 near4 thinner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:15

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34	4972	second adj3 gate adj3 (insulating or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:16
35	2922	S32 same S35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:16
36	173	S36 same thinner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/04/11 17:16